

Features

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Applications

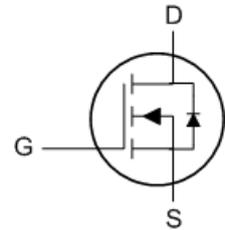
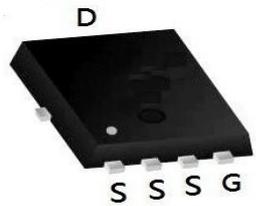
- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

Product Summary



BVDSS	RDSON	ID
40V	2.1mΩ	120A

PDFN3333-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current ¹	120	A
$I_D@T_C=100^\circ C$	Continuous Drain Current ¹	76	A
I_{DM}	Pulsed Drain Current ²	480	A
EAS	Single Pulse Avalanche Energy ³	180	mJ
I_{AS}	Avalanche Current	30	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	65.7	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State) ¹	---	60	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.9	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =G50uA	I €	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	---	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =G€A	---	G€	G€	mΩ
		V _{GS} =4.5V, I _D =F€A	---	G€	H€	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	F€G	F€	G€G	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	---	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =I €V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =I €V, V _{GS} =0V, T _J =100°C	---	---	F00	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =F€V, I _D =G€A	---	İ İ	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	F	---	Ω
Q _g	Total Gate Charge	V _{DS} =G€V, V _{GS} =F€V, I _D =G€A	---	I G€	---	nC
Q _{gs}	Gate-Source Charge		---	İ €	---	
Q _{gd}	Gate-Drain Charge		---	7.2	---	
T _{d(on)}	Turn-On Delay Time	VGS=10V, VDD=G€V, RG=3Ω, ID=G0A	---	J €	---	ns
T _r	Rise Time		---	İ €	---	
T _{d(off)}	Turn-Off Delay Time		---	H€	---	
T _f	Fall Time		---	F€	---	
C _{iss}	Input Capacitance	V _{DS} =G€V, V _{GS} =0V, f=1MHz	---	G Ğ	---	pF
C _{oss}	Output Capacitance		---	İ İ €	---	
C _{rss}	Reverse Transfer Capacitance		---	G	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	120	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	IF=20A, di/dt=100A/μs, T _J =25C	---	46	---	nS
Q _{rr}	Reverse Recovery Charge		---	18.4	---	nC

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.

2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%

3.The EAS data shows Max. rating. The test condition is VR=2I ×O, VDD=25V, VGS=10V, L=0.5mH, IAS=30A.

4.The power dissipation is limited by 150°C junction temperature

İ.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

Typical Characteristics

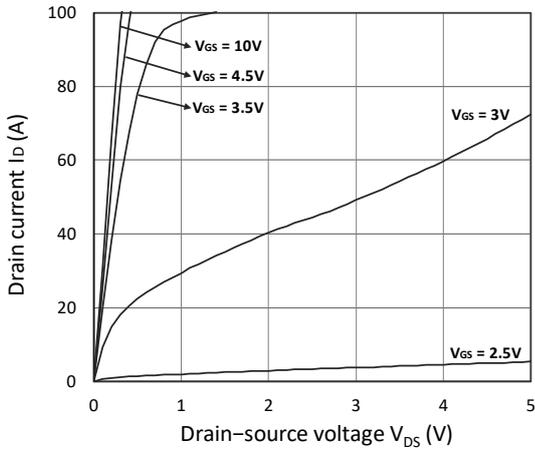


Figure 1. Output Characteristics

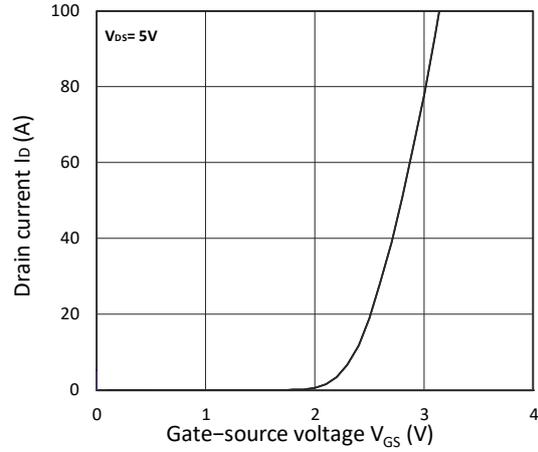


Figure 2. Transfer Characteristics

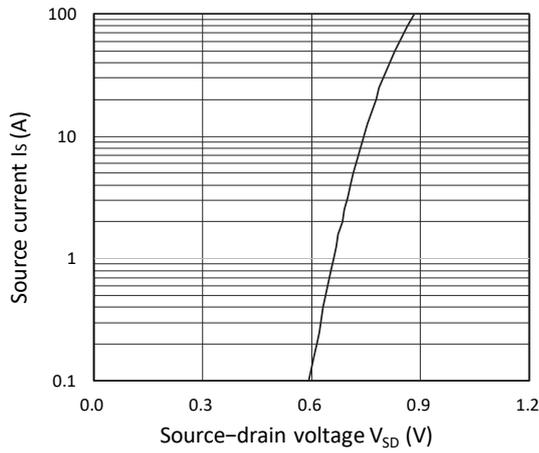


Figure 3. Forward Characteristics of Reverse

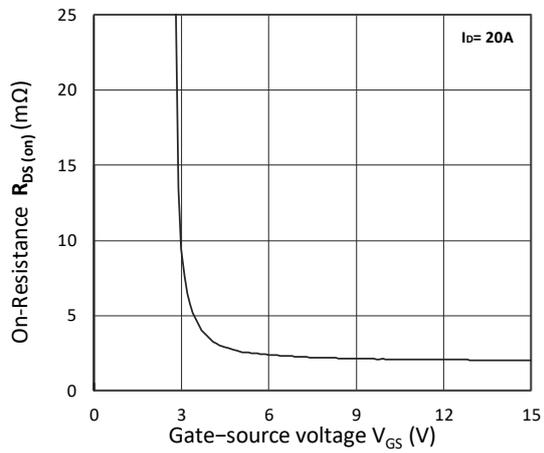


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

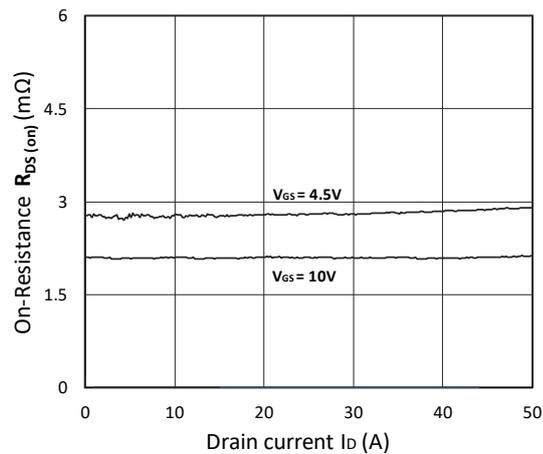


Figure 5. $R_{DS(ON)}$ vs. I_D

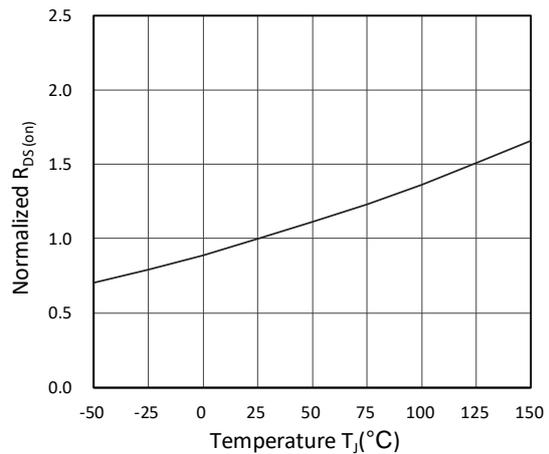


Figure 6. Normalized $R_{DS(ON)}$ vs. Temperature

N-Ch 40V Fast Switching MOSFETs

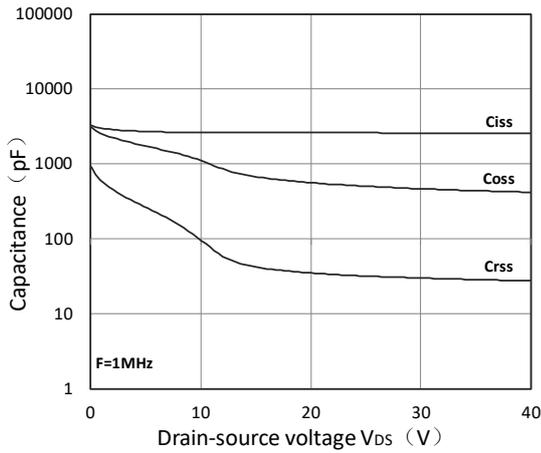


Figure 7. Capacitance Characteristics

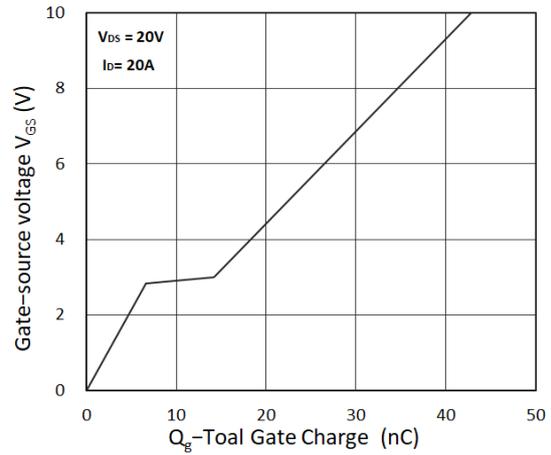


Figure 8. Gate Charge Characteristics

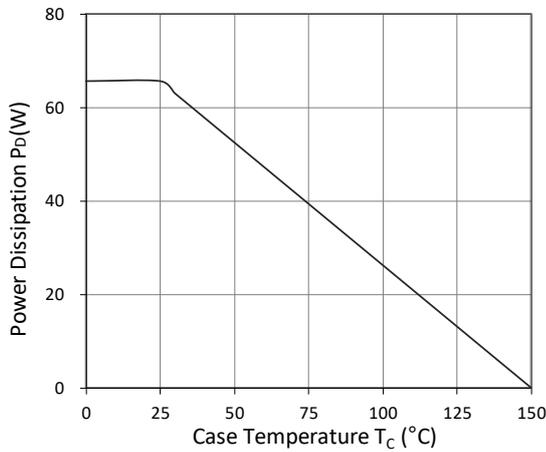


Figure 9. Power Dissipation

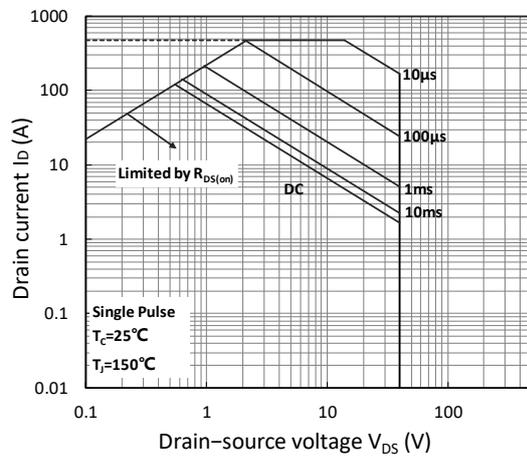


Figure 10. Safe Operating Area

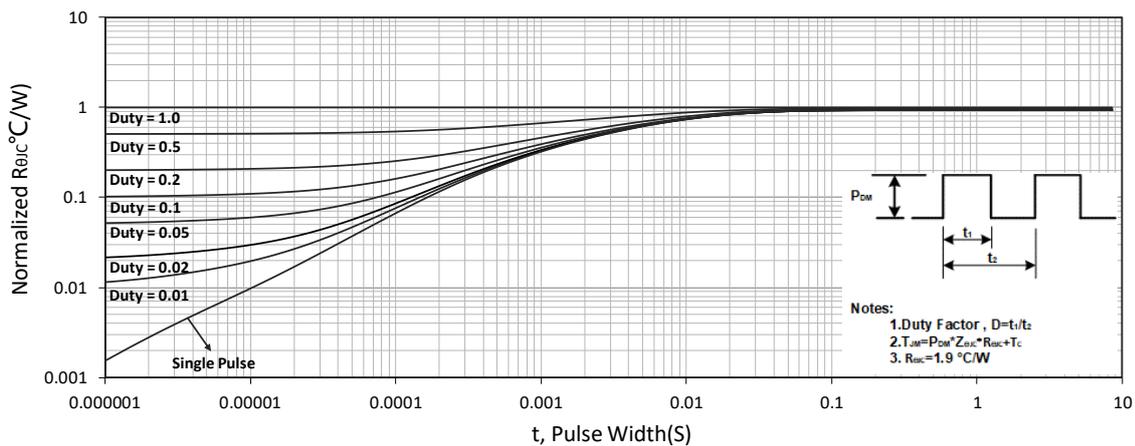


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

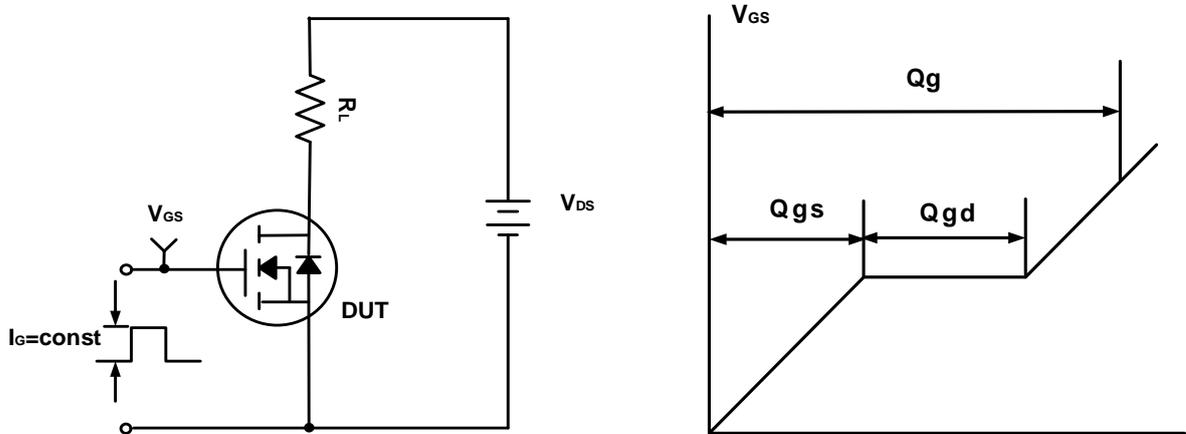


Figure A. Gate Charge Test Circuit & Waveforms

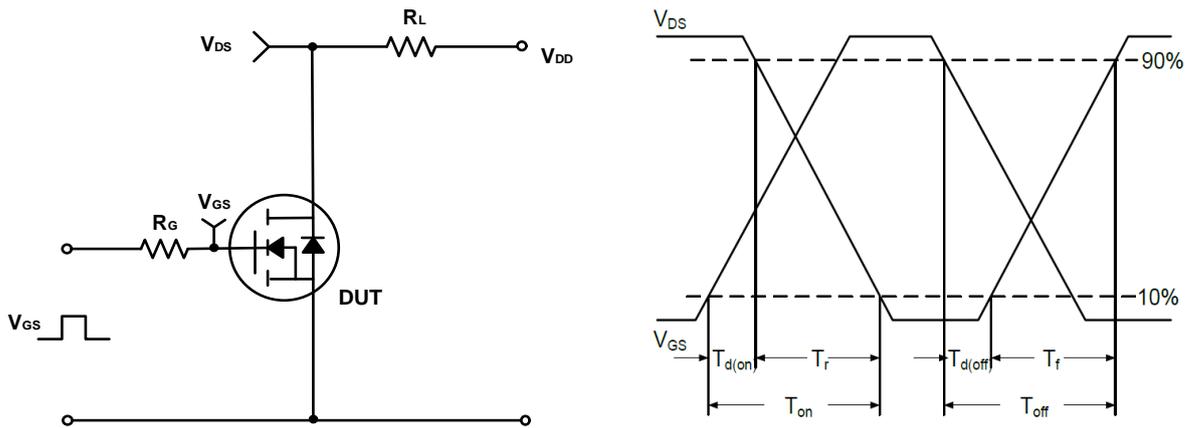


Figure B. Switching Test Circuit & Waveforms

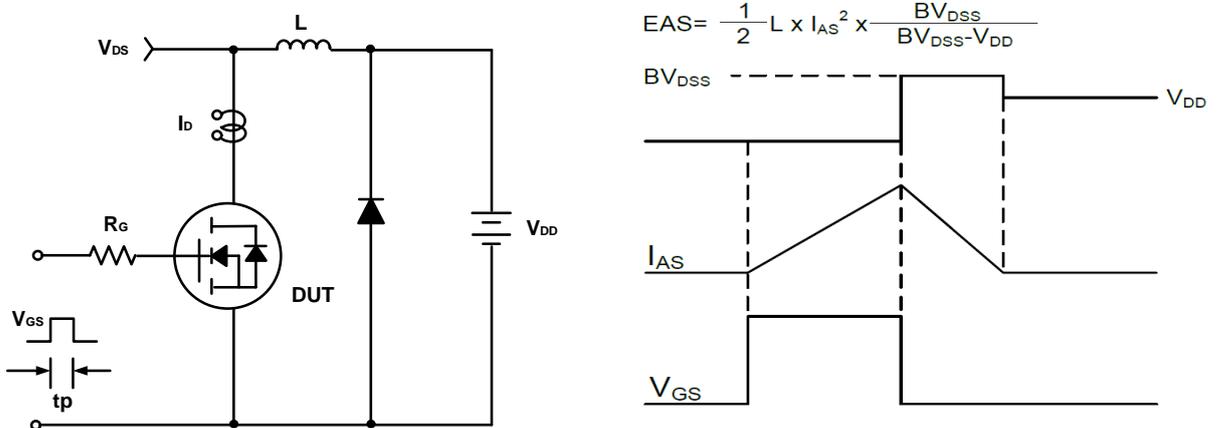
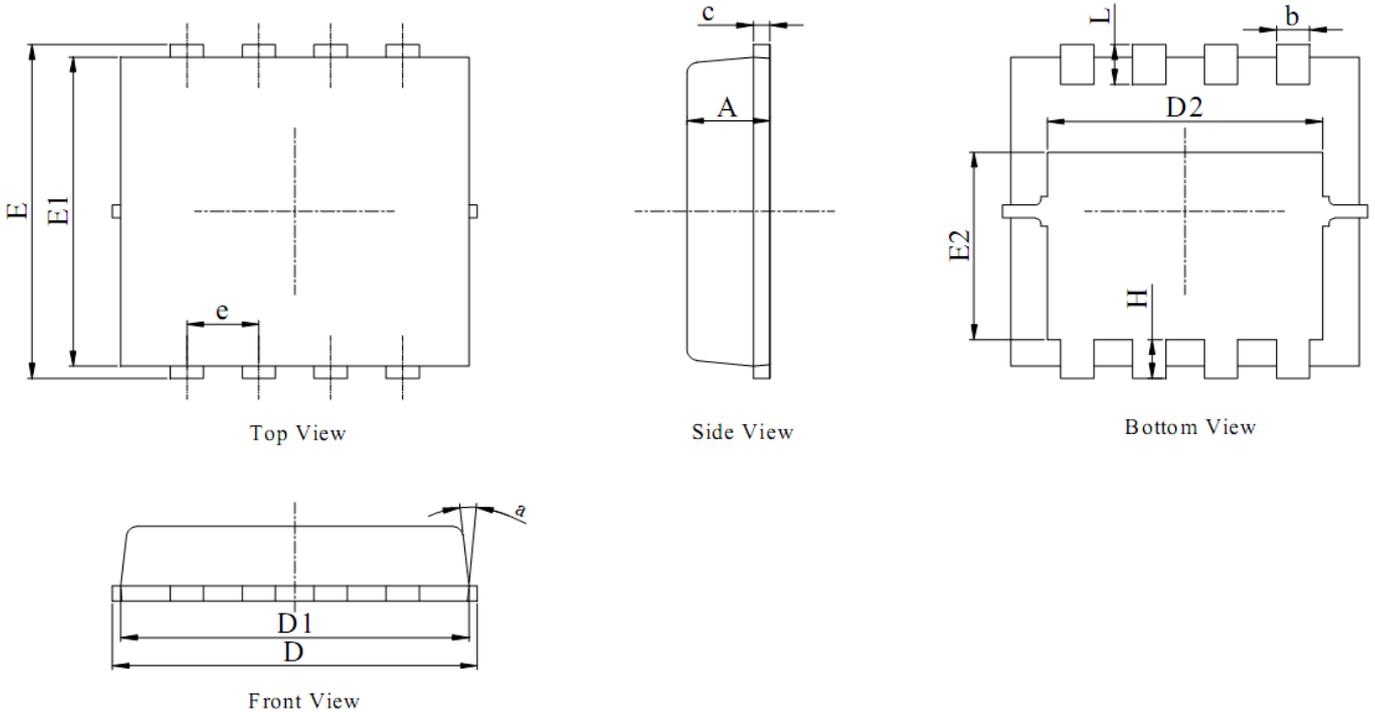


Figure C. Unclamped Inductive Switching Circuit & Waveforms

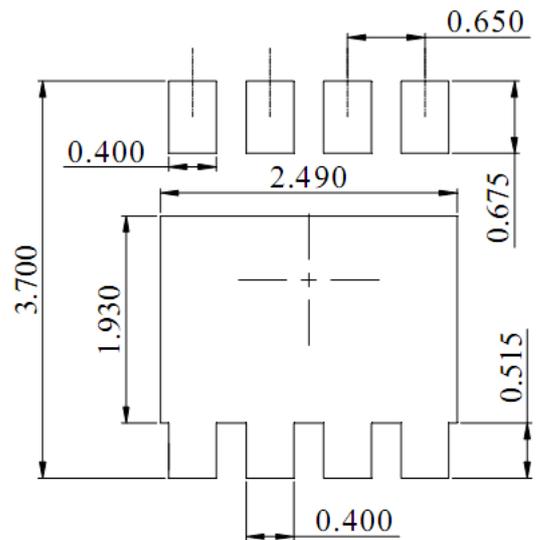
Package Mechanical Data-PDFN3333-8L-Single



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. ALL DIMENSIONS IN MILLIMETER (ANGLE IN DEGREE).
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.20	0.25
D	3.00	3.15	3.25
D1	2.95	3.05	3.15
D2	2.39	2.49	2.59
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.70	1.80	1.90
e	0.65 BSC		
H	0.30	0.40	0.50
L	0.25	0.40	0.50
a	---	---	15°



DIMENSIONS: MILLIMETERS